

## RF POWER TRANSISTOR

### DESCRIPTION:

The **ASI TAN250A** is a Common Base Transistor Designed for DME, TACAN and IFF Pulse Power Amplifier Applications.

### FEATURES INCLUDE:

- Gold Metallization
- Hermetic Package
- Input/Output Matching

### MAXIMUM RATINGS

<b>I<sub>C</sub></b>	30 A
<b>V<sub>CB</sub></b>	60 V
<b>P<sub>DISS</sub></b>	575 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>q<sub>JC</sub></b>	0.30 °C/W

PACKAGE STYLE		
	MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.890/22.61	.910/23.11
B	.640/16.26	.660/16.76
C	.053/1.35	.073/1.854
D	.115/2.921	.135/3.43
E	.130/3.30	.150/3.81
F	.100/2.54	.120/3.048
G	.395/10.03	.415/10.54
H	.052/1.321	.072/1.829
I	.440/11.18	.460/11.68
J	.376/9.550	.396/10.06
K	.183/4.65	.203/5.156
L		.170/4.318
M		.230/5.842
N	.395/10.03	.407/10.34
O	.003/0.0762	.006/0.152
P	.118/2.997	.131/3.327
Q	.050/1.27	

### CHARACTERISTICS T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 20 mA	60			V
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 25 mA      R <sub>BE</sub> = 10 Ω	60			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 20 mA	4.0			V
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 50 V			12	mA
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5 V      I <sub>C</sub> = 1.0 A	20		120	---
<b>P<sub>OUT</sub></b>	V <sub>CC</sub> = 50 V      P <sub>IN</sub> = 13 W      f = 960 to 1215 MHz Pulse Width = 20 μS      Duty Cycle = 5 %	250			W
<b>P<sub>G</sub></b>		6.0	7.0		dB
<b>h<sub>c</sub></b>			40		%